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FAIRCHILD

SEMICONDUCTOR®

November 2013

FQP13N50 N-Channel QFET® MOSFET

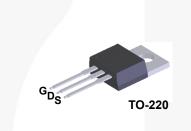
500 V, 12.5 A, 430 m Ω

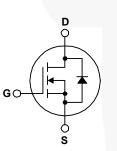
Description

This N-Channel enhancement mode power MOSFET is • 12.5 A, 500 V, $R_{DS(on)}$ = 430 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 45 nC) resistance, and to provide superior switching performance . Low Crss (Typ. 25 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- I_D = 6.25 A





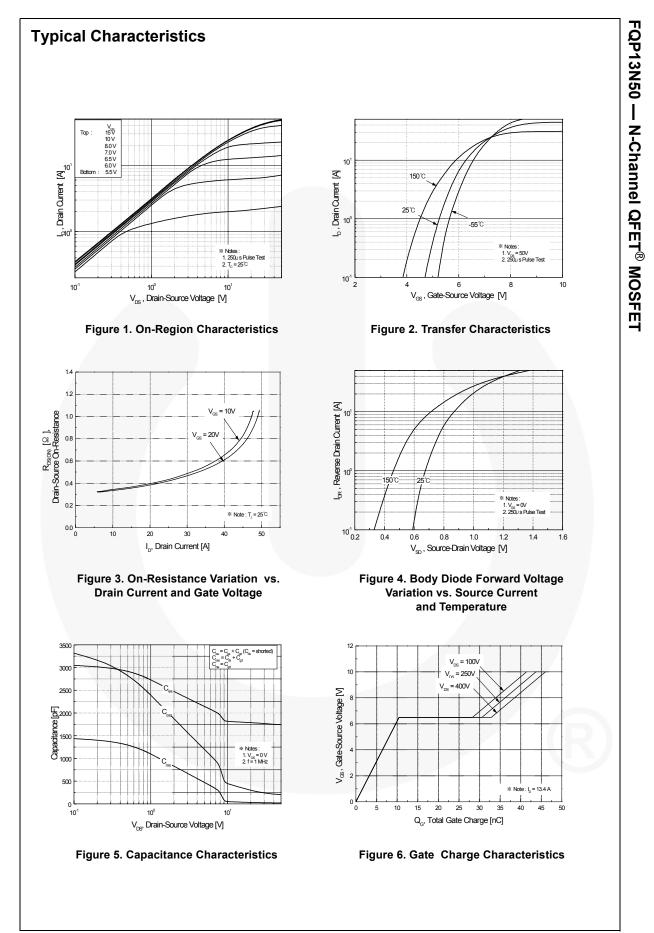
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

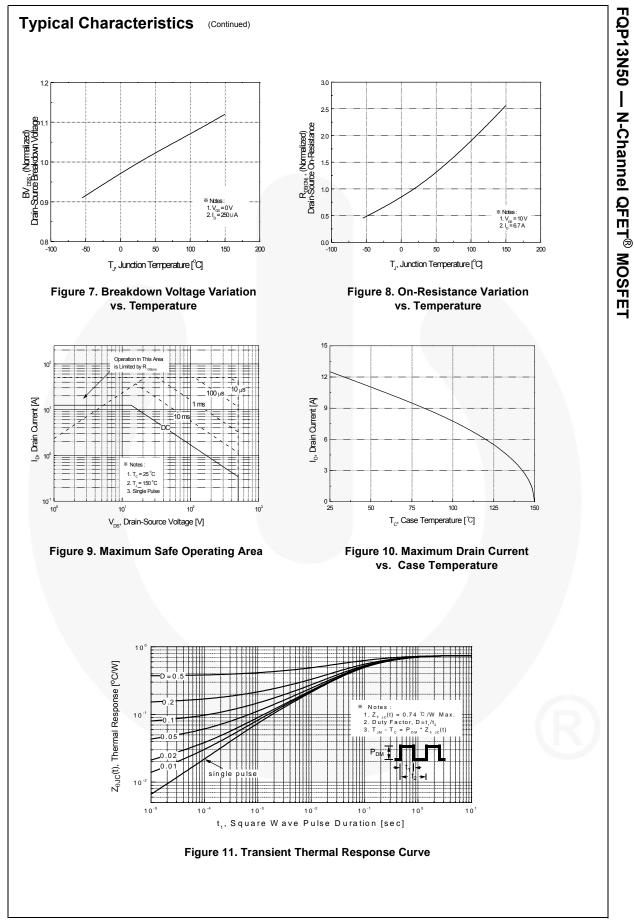
Symbol	Parameter		FQP13N50	Unit
V _{DSS}	Drain-Source Voltage		500	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		12.5	Α
	- Continuous (T _C = 100°C)		7.9	A
I _{DM}	Drain Current - Pulsed	(Note 1)	50	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	810	mJ
I _{AR}	Avalanche Current	(Note 1)	12.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	17	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
PD	Power Dissipation ($T_C = 25^{\circ}C$)		170	W
	- Derate above 25°C		1.35	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
Τ _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

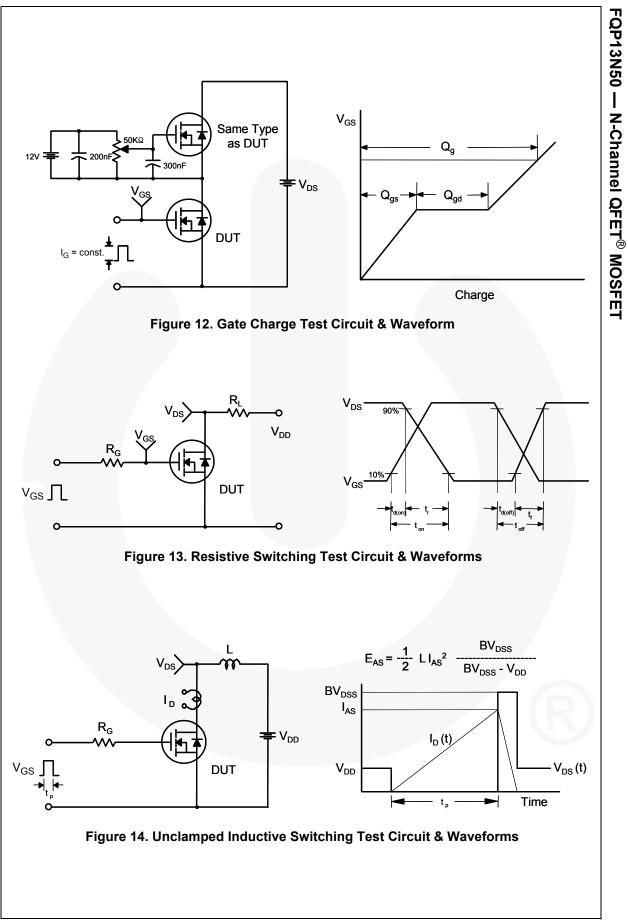
Symbol	Parameter	FQP13N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.74	°C/W
$R_{ hetaCS}$	Thermal Resistance, Case-to-Sink, Max.	0.5	°C/W

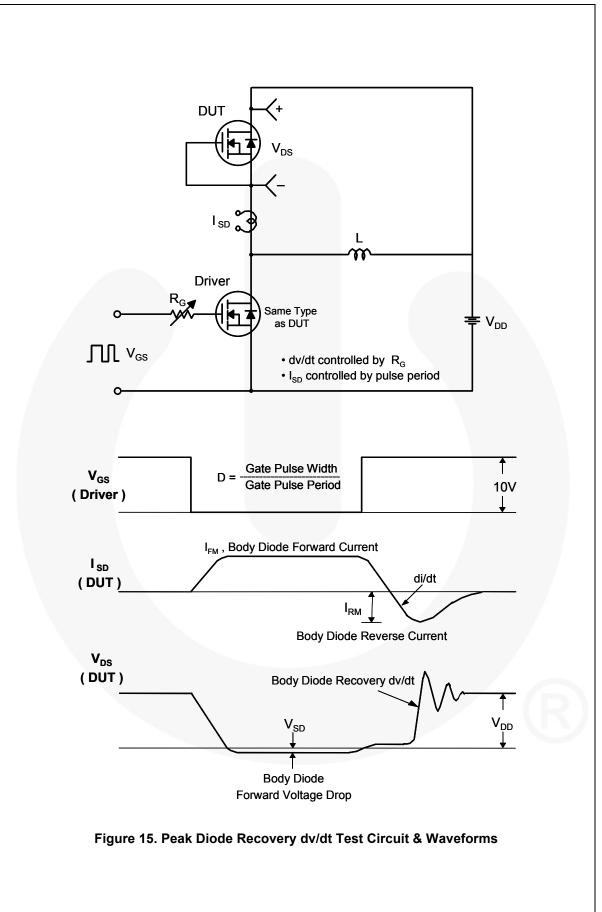
Symbol Off Cha BV _{DSS}		FQP13N50	Packaç TO-22		ing Method Tube	Reel N/		Tape Width N/A		Quantity 50 units
Off Cha BV _{DSS}	cal Char	racteristics	T _C = 25°C ur	nless otherwise no	ed.					
Off Cha BV _{DSS}	1	Parameter		Test C	onditions		Min.	Тур.	Max.	Unit
BV _{DSS}			I				1		1	
				/ _ <u>0) / I _ </u>	250 4					
		ce Breakdown Volt	0	/ _{GS} = 0 V, I _D =	250 μΑ		500			V
ΔΒV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient		ונ	I_D = 250 μ A, Referenced to 25°C				0.48		V/°C
I _{DSS}	Zero Gate Voltage Drain Current		ont	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$					1 10	μA μA
I _{GSSF}	Gate-Body	Leakage Current, I		/ _{GS} = 30 V, V _C	-				100	nA
		Leakage Current, I		/ _{GS} = -30 V, V / _{GS} = -30 V, V					-100	nA
IGSSR	Gale-Body	Leakage Current, I	Vevelse v	GS00 V, V	<u>)</u> S = 0 V				-100	IIA
On Cha	aracteristi	cs								
V _{GS(th)}	Gate Thres	shold Voltage	V	/ _{DS} = V _{GS} , I _D :	= 250 μA		3.0		5.0	V
R _{DS(on)}	Static Drain On-Resista		V	/ _{GS} =10 V, I _D =	6.25A			0.33	0.43	Ω
9 _{FS}	Forward Tr	ansconductance	V	/ _{DS} = 50 V, I _D	= 6.25 A			10		S
Dynam	ic Charac	torictics						I	1	
C _{iss}	Input Capa							1800	2300	pF
C _{oss}	Output Capa			$V_{\rm DS} = 25 \rm V, V_{\rm C}$	_S = 0 V,			245	320	pr
C _{rss}		ansfer Capacitance		= 1.0 MHz				245	35	pr
	ing Chara	atoristics							00	pi
Switch t _{d(on)}	ing Chara Turn-On De	elay Time	v	/ _{DD} = 250 V, I _I	₀ = 13.4 A,			40	90	ns
Switch t _{d(on)} t _r	Turn-On De Turn-On Ri	elay Time ise Time		/ _{DD} = 250 V, Ι _[R _G = 25 Ω) = 13.4 A,			140	90 290	ns
Switch t _{d(on)} t _r t _{d(off)}	Turn-On De Turn-On Ri Turn-Off De	elay Time ise Time elay Time				()		140 100	90 290 210	ns ns ns
Switch t _{d(on)} t _r t _{d(off)} t _f	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa	elay Time ise Time elay Time all Time	F	R _G = 25 Ω		(Note 4)		140 100 85	90 290 210 180	ns ns ns ns
Switch $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate	elay Time ise Time elay Time all Time Charge	F	R _G = 25 Ω V _{DS} = 400 V, I _E		(Note 4)	 	140 100 85 45	90 290 210 180 60	ns ns ns ns nC
Switch t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs}	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source	elay Time ise Time elay Time all Time Charge ce Charge	F	R _G = 25 Ω) = 13.4 A,	· ·	 	140 100 85 45 11	90 290 210 180 60 	ns ns ns ns nC nC
Switch t _{d(on)} t _r td(off) t _f Q _g Q _{gs} Q _{gd}	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Sourc Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge o Charge	F	R _G = 25 Ω / _{DS} = 400 V, I _C / _{GS} = 10 V) = 13.4 A,	(Note 4) (Note 4)	 	140 100 85 45	90 290 210 180 60	ns ns ns ns nC
Switch t _{d(on)} t _r td(off) t _f Q _g Q _{gs} Q _{gd}	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge	stics and	R _G = 25 Ω / _{DS} = 400 V, I _C / _{GS} = 10 V Maximum	9 = 13.4 A, Ratings	· ·	 	140 100 85 45 11	90 290 210 180 60 	ns ns ns ns nC nC
Switch $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g Q_{gs} Q_{gd} Drain-S	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain	elay Time ise Time elay Time all Time Charge ce Charge Charge Ode Characteri	stics and Source Diode	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ Maximum Forward Curr	9 = 13.4 A, Ratings	· ·	 	140 100 85 45 11 22	90 290 210 180 60 	ns ns ns nC nC nC
Switch $t_{d(on)}$ t_r $t_{d(off)}$ t_f Q_g Q_{gs} Q_{gd} Drain-S	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain Source Dic Maximum F	elay Time ise Time elay Time all Time Charge ce Charge Charge Ode Characteri Continuous Drain-S	stics and Gource Diode ce Diode For	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ Maximum Forward Curr	p = 13.4 A, Ratings ent	<u> </u>	 	140 100 85 45 11 22	90 290 210 180 60 12.5	ns ns ns nC nC nC A
Switch t _{d(on)} t _r t_d(off) t _f Q _g Q _{gs} Q _{gd} Drain-S I _{SM}	Turn-On De Turn-On Ri Turn-Off De Turn-Off Fa Total Gate Gate-Source Gate-Drain Source Dic Maximum (Maximum F Drain-Source	elay Time ise Time elay Time all Time Charge ce Charge c Charge Ode Characteri Continuous Drain-S Pulsed Drain-Sourc	stics and Source Diode Diode Forn Voltage V	$R_{G} = 25 \Omega$ $V_{DS} = 400 V, I_{C}$ $V_{GS} = 10 V$ Maximum Forward Current	ent 12.5 A	<u> </u>	 	140 100 85 45 11 22	90 290 210 180 60 12.5 50	ns ns ns nC nC nC A A

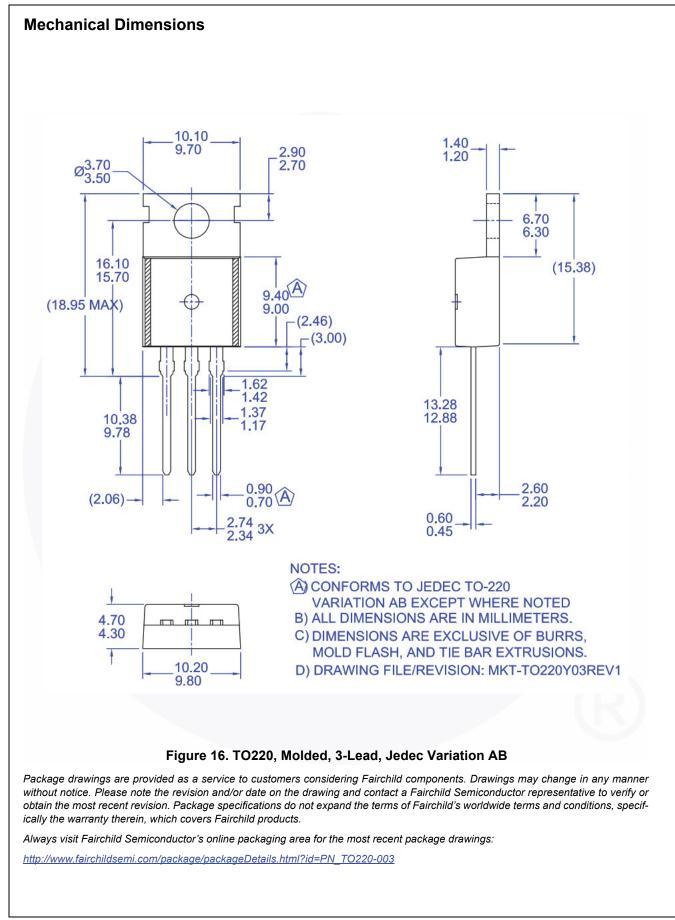




©2000 Fairchild Semiconductor Corporation FQP13N50 Rev. C1







FQP13N50 — N-Channel QFET[®] MOSFET



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Preliminary

No Identification Needed

Obsolete

First Production

Full Production

Not In Production

notice to improve design.

Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without

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Rev. 166

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